



IRLZ14STRLPBF Information



For Reference Only

Part Number IRLZ14STRLPBF Manufacturer Vishay Siliconix

Category Discrete Semiconductor Products
Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 60V 10A D2PAK

Package TO-263-3, D2Pak (2 Leads + Tab), TO-263AB

For the pricing/inventory/lead time, please contact

us

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IRLZ14STRLPBF Specifications

Manufacturer Part NumberIRLZ14STRLPBFManufacturerVishay SiliconixCategoryDiscrete Semiconductor ProductsTransistors - FETs, MOSFETs - SinglePackageTO-263-3, D2Pak (2 Leads + Tab), TO-263ABSeries-FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)60VCurrent - Continuous Drain (Id) @ 25°C10A (Tc)Drive Voltage (Max Rds On, Min Rds On)4V, 5VVgs(th) (Max) @ Id2V @ 250μAGate Charge (Qg) (Max) @ Vgs8.4nC @ 5VInput Capacitance (Ciss) (Max) @ Vds400pF @ 25VVgs (Max)±10VFET Feature-
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-263-3, D2Pak (2 Leads + Tab), TO-263AB Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single TO-263-AB TO-263-3, D2Pak (2 Leads + Tab), TO-263AB Series - N-Channel N-C
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Input Capacitance (Ciss) (Max) @ Vds
Vgs (Max) ±10V FET Feature -
FET Feature -
Power Dissipation (Max) 3.7W (Ta), 43W (Tc)
Rds On (Max) @ Id, Vgs 200 mOhm @ 6A, 5V
Operating Temperature $-55^{\circ}\text{C} \sim 175^{\circ}\text{C} \text{ (TJ)}$
Mounting Type Surface Mount
Supplier Device Package D2PAK
Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB
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IRLZ14STRLPBF Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

IRLZ14STRLPBF Payment Methods





















IRLZ14STRLPBF Shipping Methods













If you have any question about IRLZ14STRLPBF, please do not hesitate to contact us!

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